



High-Voltage Switching Applications

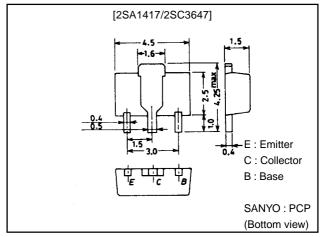
Features

- · Adoption of FBET, MBIT processes.
- · High breakdown voltage and large current capacity.
- · Fast switching time.
- · Very small size making it easy to provide highdensity, small-sized hybrid ICs.

Package Dimensions

unit:mm

2038



(): 2SA1417

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)120	V
Collector-to-Emitter Voltage	VCEO		(-)100	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	IC		(-)2	Α
Collector Current (Pulse)	I _{CP}		(-)3	Α
Collector Dissipation	PC		500	mW
		Moutned on ceramic board (250 ² ×0.8mm)	1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

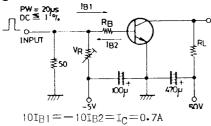
Description	O: : h l	0 19		Ratings		
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)100V, I _E =0			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(–)100	nA
DC Current Gain	h _{FE}	V _{CE} =(-)5V, I _C =(-)100mA	100*		400*	
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)100mA		120		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(25)		pF
				16		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)1A, I _B =(-)100mA		(-0.22)	(-0.6)	V
				0.13	0.4	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)1A, I _B =(-)100mA		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =(-)10μA, I _E =0	(–)120			V
Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =(-)1mA, R _{BE} =∞	(–)100			V
Emitter-to-Base Breakdown Votage	V _{(BR)EBO}	I _E =(-)10μΑ, I _C =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit.		(80)		ns
				80		ns
Stotage Time	t _{stg}	See specified Test Circuit.		(750)		ns
				1000		ns
Fall Time	t _f	See specified Test Circuit.		(40)		ns
				50		ns

 $\mbox{*}$: The 2SA1417/2SC3647 are classified by 100mA \mbox{h}_{FE} as follows :

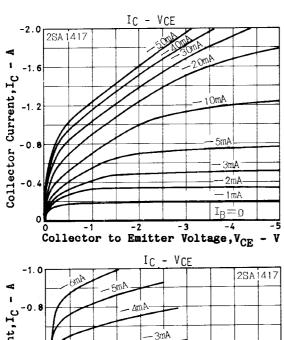
	100	R	200	140	S	280	200	Т	400
Marking 2SA	h	E ra	nk : R,	S, T					

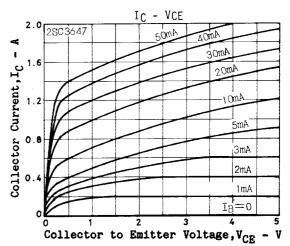
2SC3647 : CC

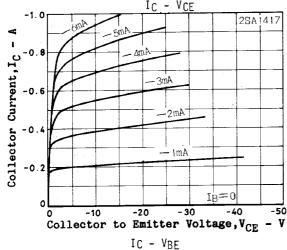
Switching Time Test Circuit

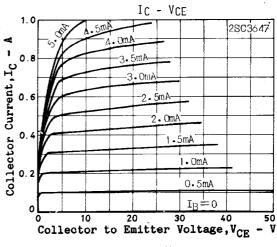


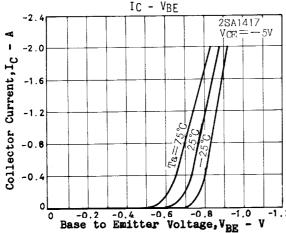
(For PNP, the polarity is reversed) Unit (resistance : Ω , capacitance : F)

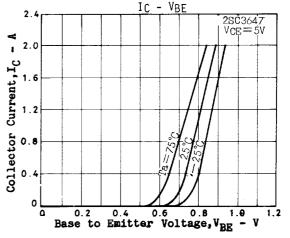


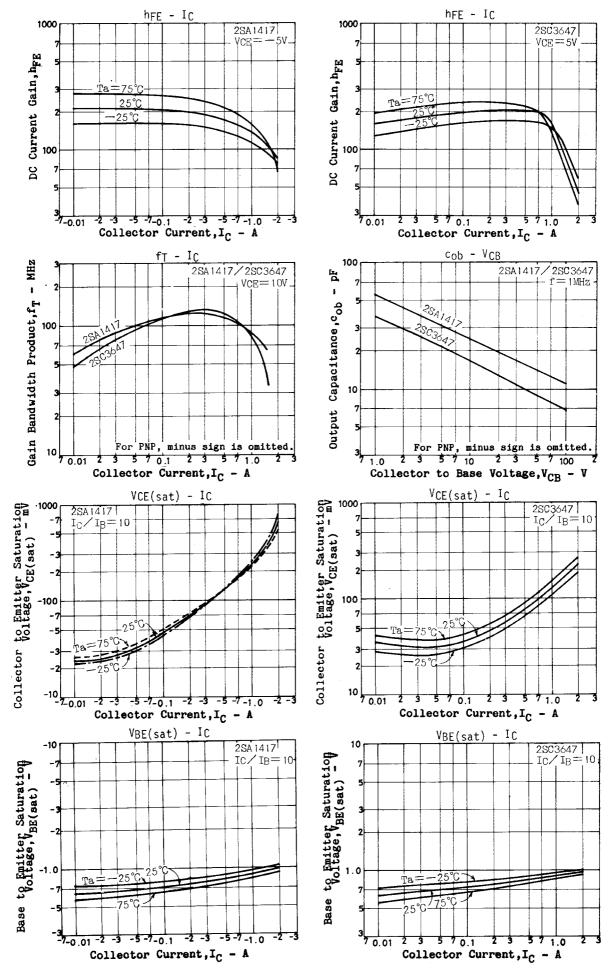




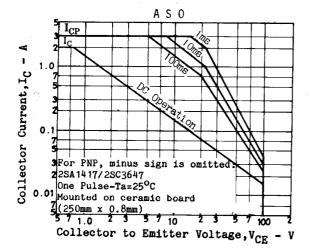


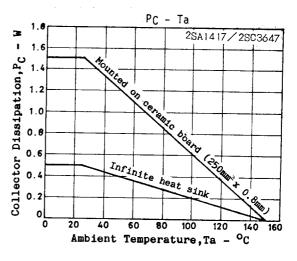






2SA1417/2SC3647





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